- 3. The mesoporous silica film as recited in claim 1, wherein said thickness has a standard deviation less than +/- 5%.
- 4. The mesoporous silica film as recited in claim 1, wherein a porosity of said mesoporous silica film is disordered.
- 5. A mesoporous silica film having a thickness from about 0.1 μ m to about 1.5 μ m and a standard deviation about said thickness, wherein said standard deviation is less than +/- 5%.

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6. The mesoporous silica film as recited in claim 5, wherein a dielectric constant of said mesoporous silica film is less than 3.

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7. The mesoporous silica film as recited in claim 5, having a dielectric constant with a relative stability and an absolute stability.

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8. The mesoporous silica film as recited in claim 5, having an average pore size less than or equal to about 20 nm.

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9. The mesoporous silica film as recited in claim 5, having a porosity that is disordered.

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- 10. A mesoporous silica film prepared from a surfactant containing solution, comprising a porosity that is disordered, said porosity having an average pore diameter of less than or equal to about 20 nm, and a film thickness from about 0.1 μ m to about 1.5 μ m.
- 11. The mesoporous silica film as recited in claim 10, having a dielectric constant less than 3, said dielectric constant having both a relative stability and an absolute stability.

Cancel claims 12-52

Application No. 09/837,885

PAGE 2

MJM Do. No. 1941-76

15 AZ. A mesoporous silica film characterized by:

a disordered porosity, lacking a regular geometric arrangement of pores, and characterized by an x-ray diffraction peak between about 0.75 and about 2 degrees 2-theta:

a dielectric constant less than 3.0 that is stable; a film thickness from about 0.1 μm to about 1.5 μm; and an average pore diameter less than or equal to about 20 nm.

13. A mesoporous silica film characterized by:
a disordered porosity as indicated by an absence of an XRD peak in the range
from 2 to 6 degrees 2-theta;

a dielectric constant less than 3.0 that is stable; a film thickness from about 0.1 μm to about 1.5 μm; and an average pore diameter less than or equal to about 20 nm.

14. A mesoporous film characterized by:
a dielectric constant less than 3.0 that is stable;
a film thickness from about 0.1 μm to about 1.5 μm; and
an average pore diameter less than or equal to about 20 nm.

Cancel claims 56-65

15. A mesoporous film having a dielectric constant less than 2.5, a film thickness from about 0.2 μm to about 1.5 μm, and an average pore diameter less than or equal to about 5 nm.

16. A mesoporous film having a thickness from about 0.2 μm to about 1.5 μm and a standard deviation about said thickness that is less than +/- 5%.

Application No. 09/837.885

PAGE 3

MJM Do. No. 1941-76

- 17. A mesoporous silica film prepared from a surfactant containing solution, having a dielectric constant less than 3 that has both a relative stability and an absolute stability in a humid atmosphere, a film thickness from about 0.1 μm to about 1.5 μm, an average pore diameter less than or equal to about 20 nm, and a porosity that is disordered.
- 2 18. The mesoporous silica film as recited in claim 17, wherein disordered is indicated by the absence of an X-ray diffraction peak in the range of about 2 to about 6 degrees 2-theta.

19. The mesoporous silica film as recited in claim 17, wherein disordered porosity is characterized by an X-ray diffraction peak between about 0.75 and about 2 degrees 2-theta.

Cancel claims 71-74

20. A surfactant-templated mesoporous dielectric film on a substrate prepared from a silica precursor solution by evaporation, wherein the film is characterized by disordered porosity.

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- 21. The dielectric film of claim 20, wherein the silica precursor includes one or more of methyl and ethyl groups.
 - The dielectric film of claim 20, wherein the silica precursor includes one or more of alkyl and phenyl groups.
 - 23. The dielectric film of claim 20, wherein the silica precursor includes carbon-containing groups.

Application No. 09/837,885

PAGE 4

MJM Do. No. 1941-76